

Monolithic CMOS ASIC Developments

11th "Trento" Workshop on Advanced Silicon Radiation Detector

Talk: HVCMOS 1 / 153

SLAC National Accelerator Laboratory

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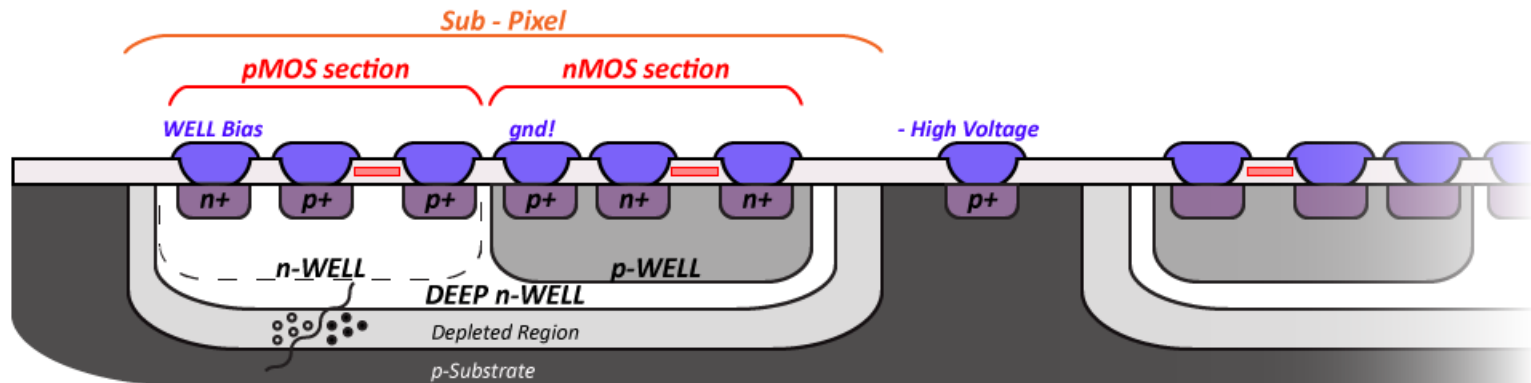
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- **Monolithic CMOS ASIC**
- **Motivations**
- **CHESS-2 : CMOS HV Evaluation for Strip Sensors**
- **COOL-1: CMOS fOr Outer Layers ASIC**
- **KPiXM: ECal read-out of Silicon Detector for ILC**

Monolithic CMOS ASIC

AMS 0.35 μm HV



Sensor and read-out on the same substrate.

Motivations from a Science perspective

Monolithic technologies have the potential for providing higher granularity, thinner, intelligent detectors at lower overall cost:

- **Significantly lower material budget**
 - eliminate the need for bump bonding or other challenging interconnect methods
 - can be thinned to less than 100um
- **Smaller pixel size**
 - not limited by bump bonding
- **Lower costs**
 - can be implemented in standard commercial technologies

	Hybrid	Depleted MAPS	
		HVCMOS	HRCMOS
collection speed	fast (drift)	fast (partial/drift)	fast (drift)
cost	high	low	low
material	high	low	low
pixel size	medium	small	small
signal	high	low	high
In pix processing	high	Medium/high	high

Monolithic technologies for Particle Physics Application



We have an interest in monolithic technologies for applications in Particle Physics:

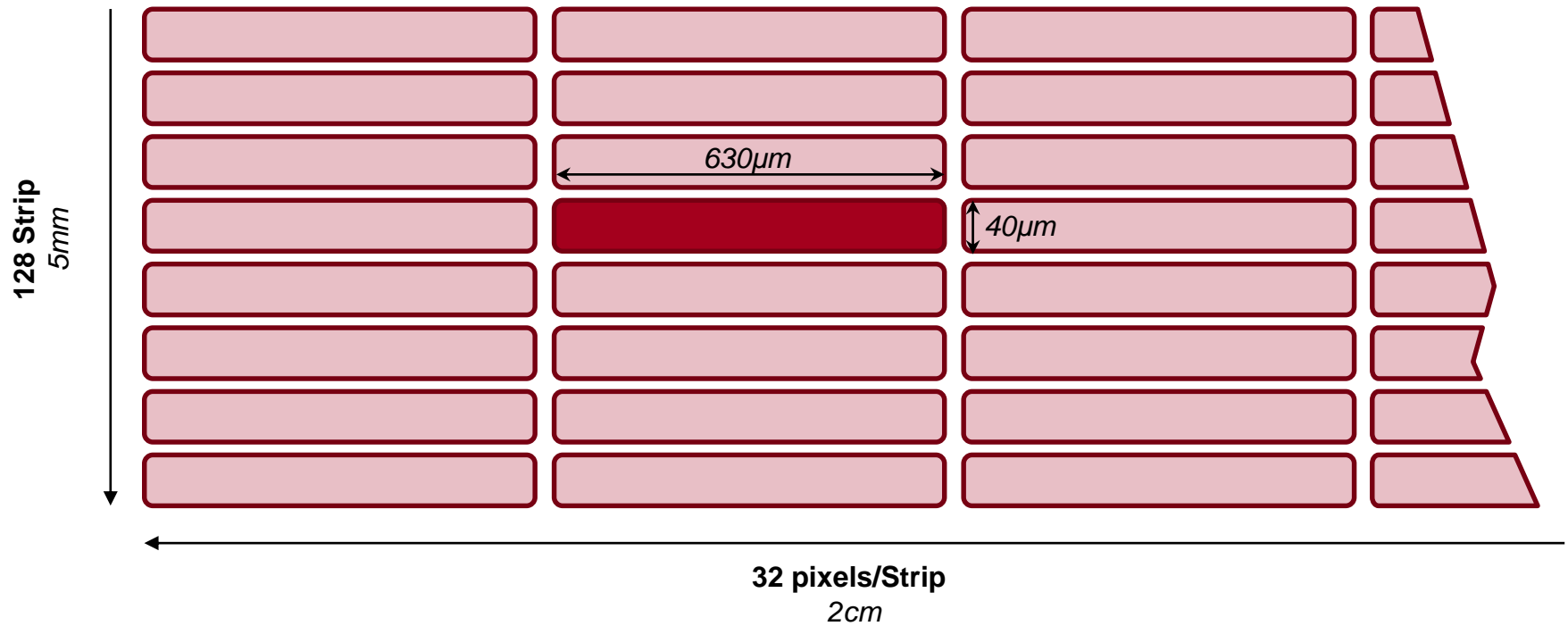
- ATLAS Strips (**CHESS2** in collaboration with UCSC)
- ATLAS Outer Pixels (**COOL**)
- ILC SiD Tracker and Ecal (**KPiXM**)

- **Demonstrate HVCMOS as a viable solution for ATLAS strip detector.**
 - *Record hits on full reticle sensor 128 strips – 32 sub-pixels*
 - *Amplify, filter and discriminate signal*
 - *Encode hit position in sensor and send to external readout electronics*
- **Further investigate performances of HVCMOS MAPS sensors**
 - *Size close to final sensor : test beams, module assembly, etc..*
 - *Evaluate sensors with different substrate resistivity 20, 50-100, 200-300, 600-2000 Ohm-cm.*
 - *Study radiation hardness using test structures.*
 - *Characterize the pixel arrays with different methods, include edge-TCT and beam tests*
 - *Large scale effects: common noise, cross-talk, power drops etc..*

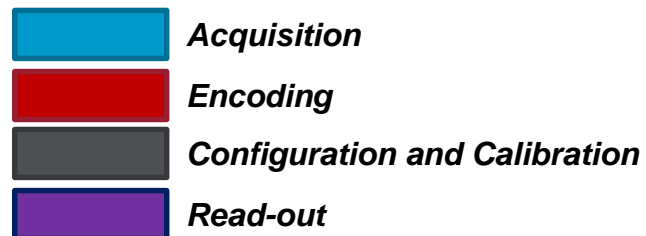
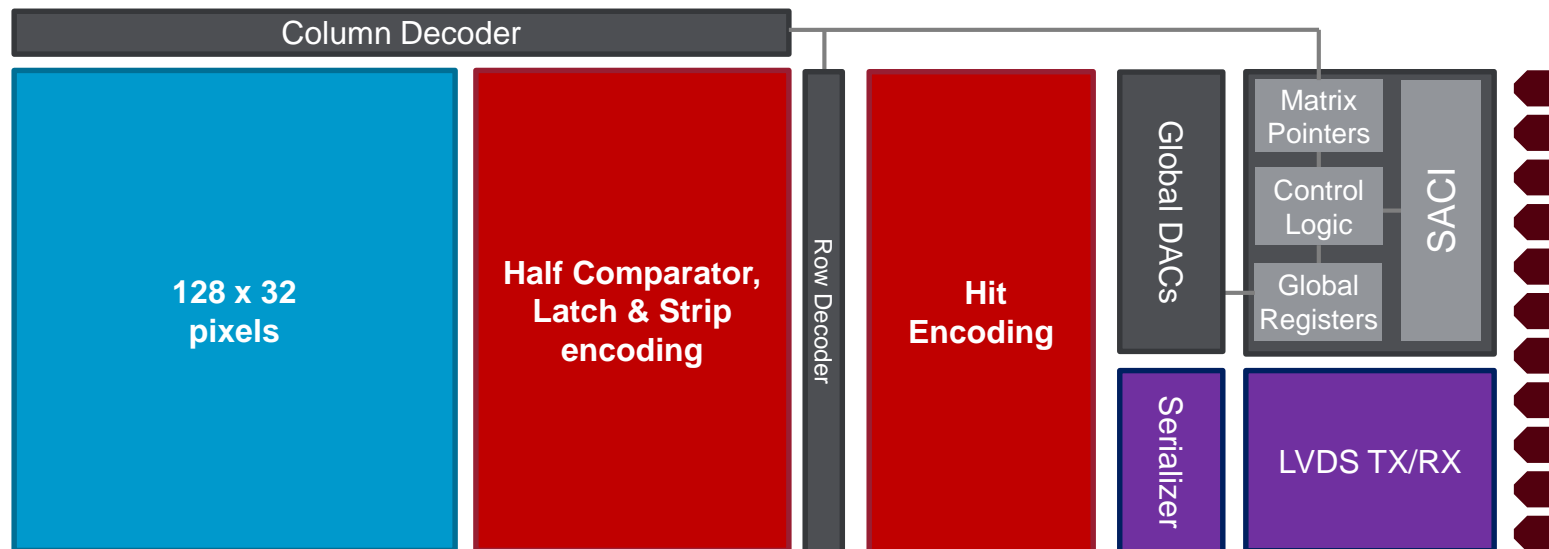
CHESS2 - Specifications

	Specs	Comments
Substrate resistivity	20Ohms to 1000Ohms	<i>Minimal MIP from from 1500e to 4000e</i>
Substrate high voltage bias	120V	<i>40% more charge vs 60V</i>
Pixel size	40 μ m x 630 μ m	<i>400fF det. capacitance</i>
Number of pixel per strip	32	
Number of strips	128	<i>Factor ~2 improvement in r-phi resol.</i>
Timing resolution	25ns	
Maximum number of hits per strip	1 + flag	
Maximum number of hits per 128 strips	8	
Readout speed	320MHz	
Number of wire bonds	28/128strips (data only)	<i>x5 reduction</i>
Additional constraint	Rad-hard design	<i>Periphery: dead area 4mm - shorter strips</i>

CHESS2: Strip sensor size

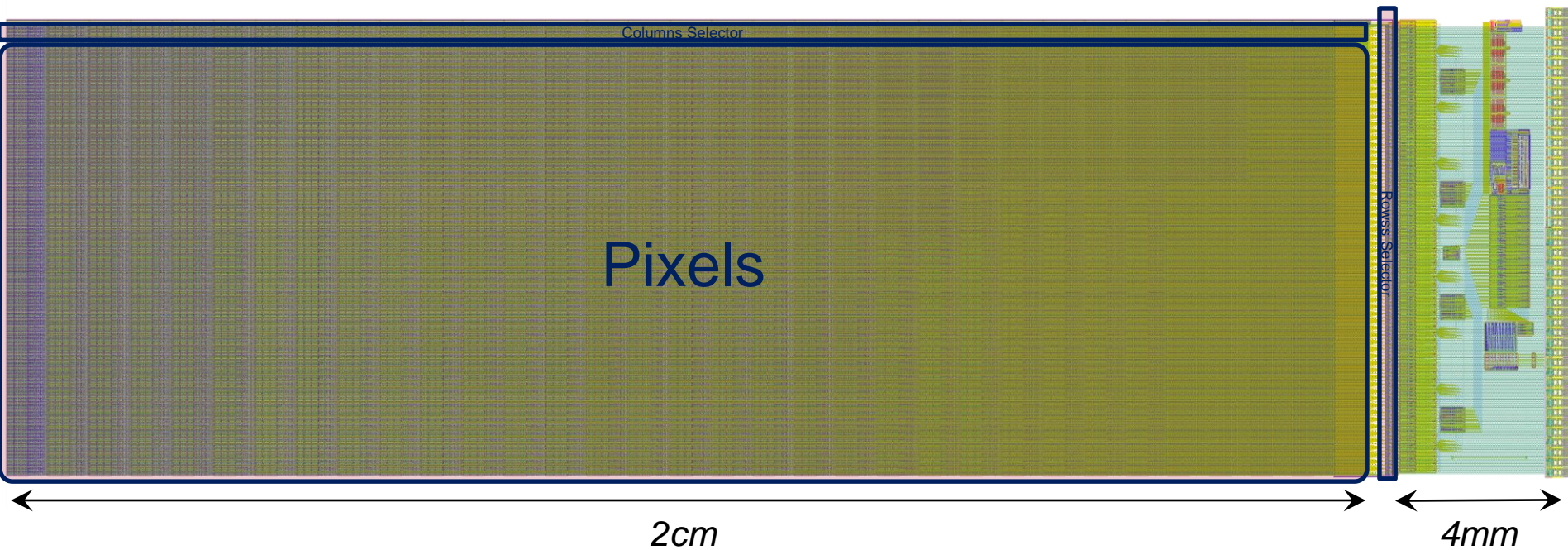


CHESS2: ASIC Architecture



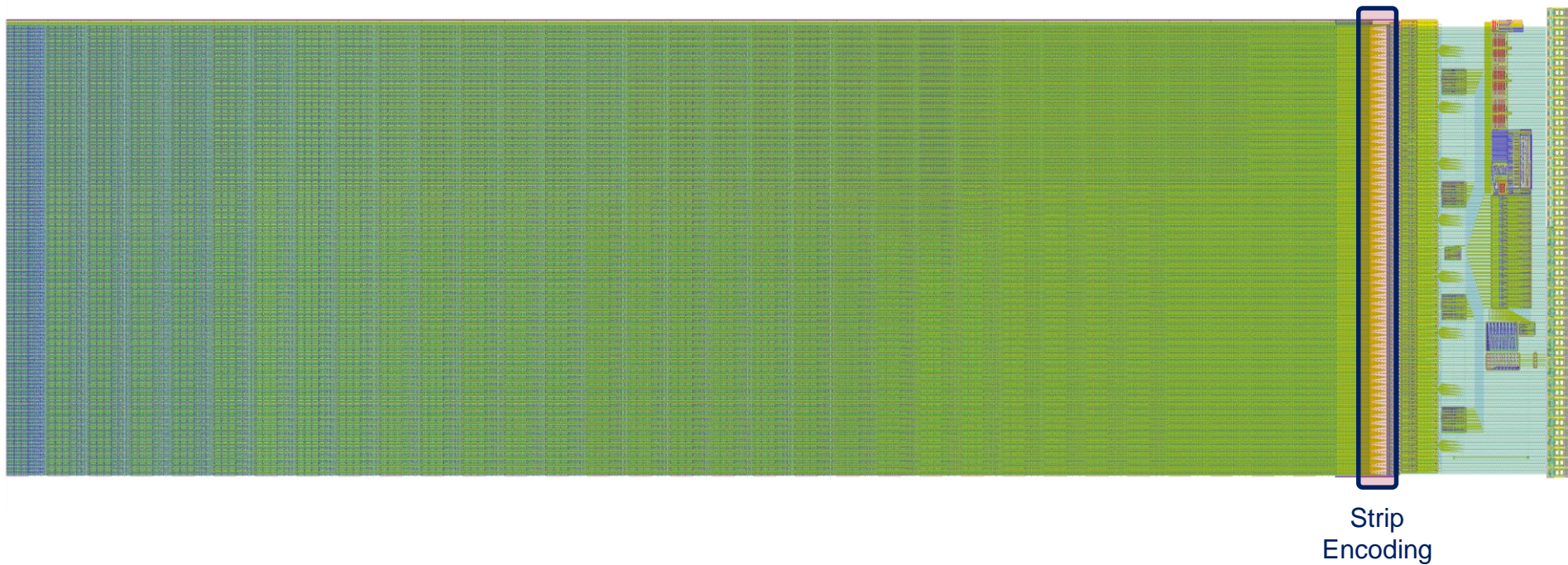
CHESS2 Floor Plan

Pixels – Row, Column selectors



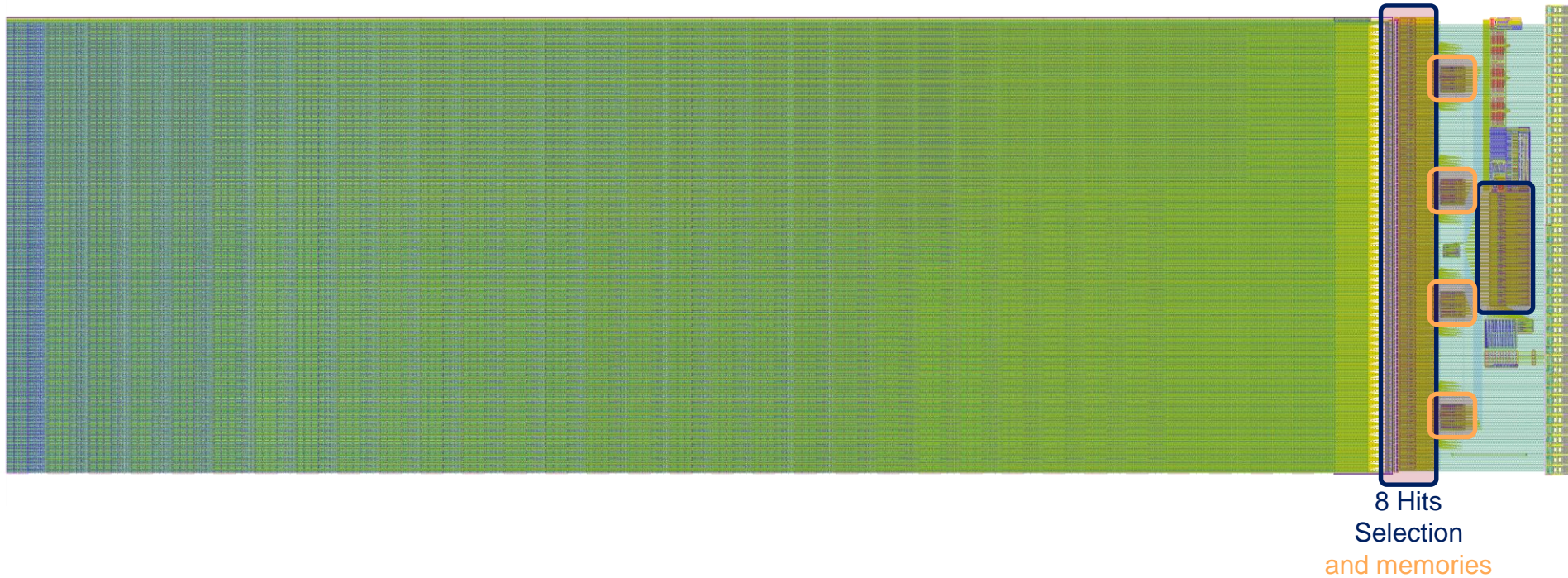
CHES2 Floor Plan

Strip Encoding



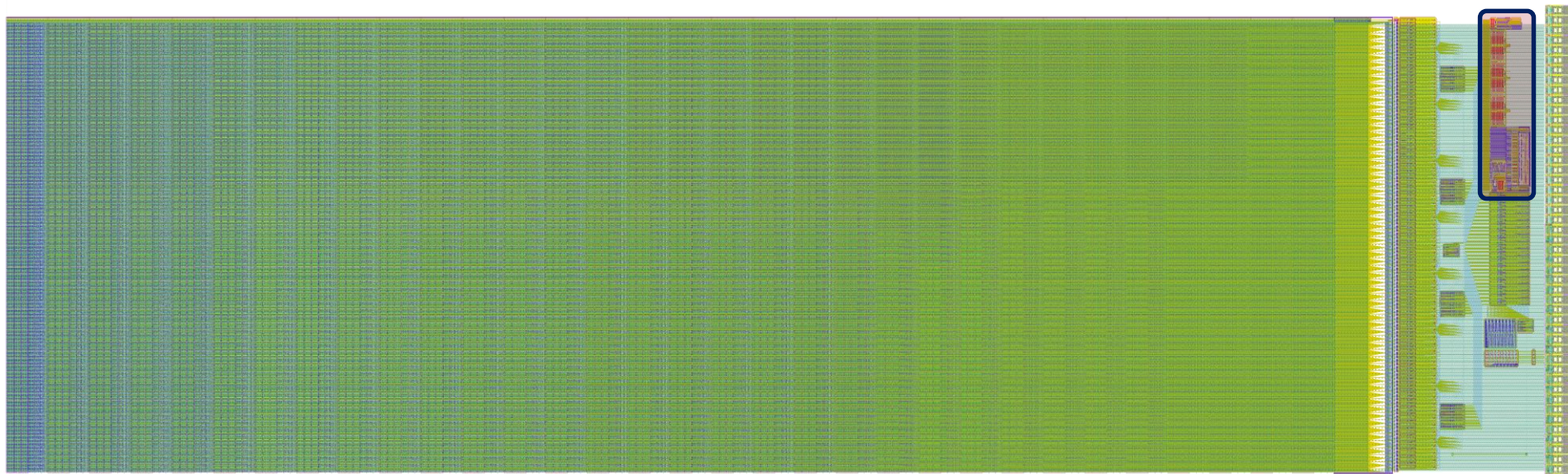
CHES2 Floor Plan

8 Hit Encoding Logic & Memories



CHES2 Floor Plan

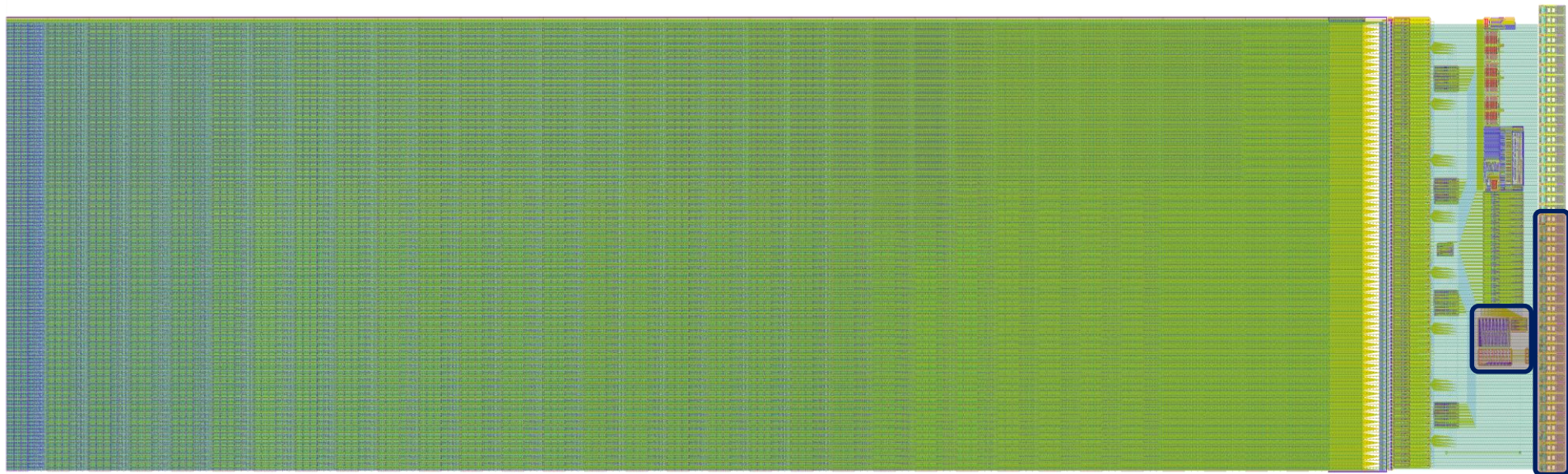
SACI – Registers – Current sources



SACI &
Current sources

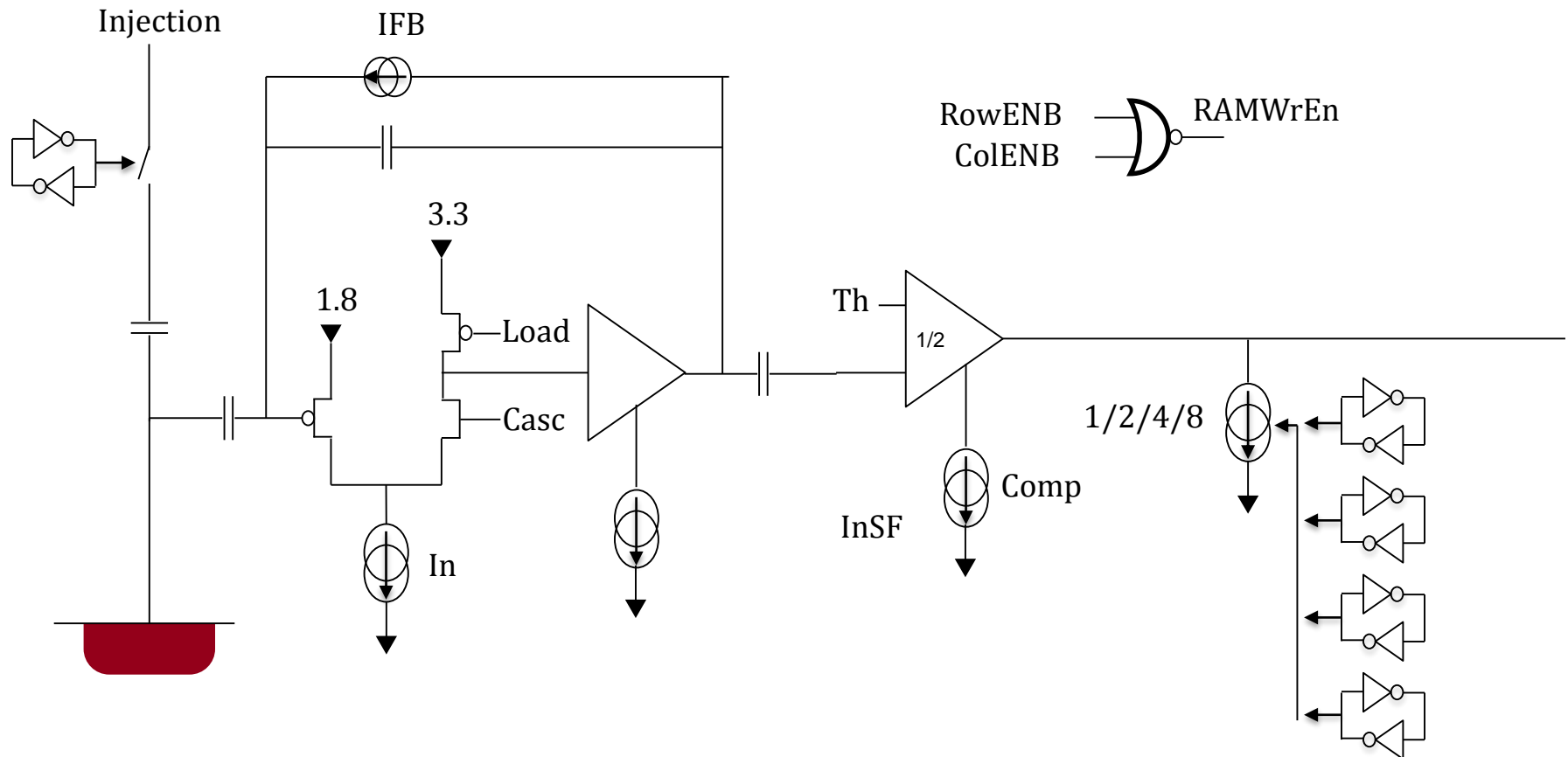
CHESS2 Floor Plan

Serializer – LVDS TX/RX

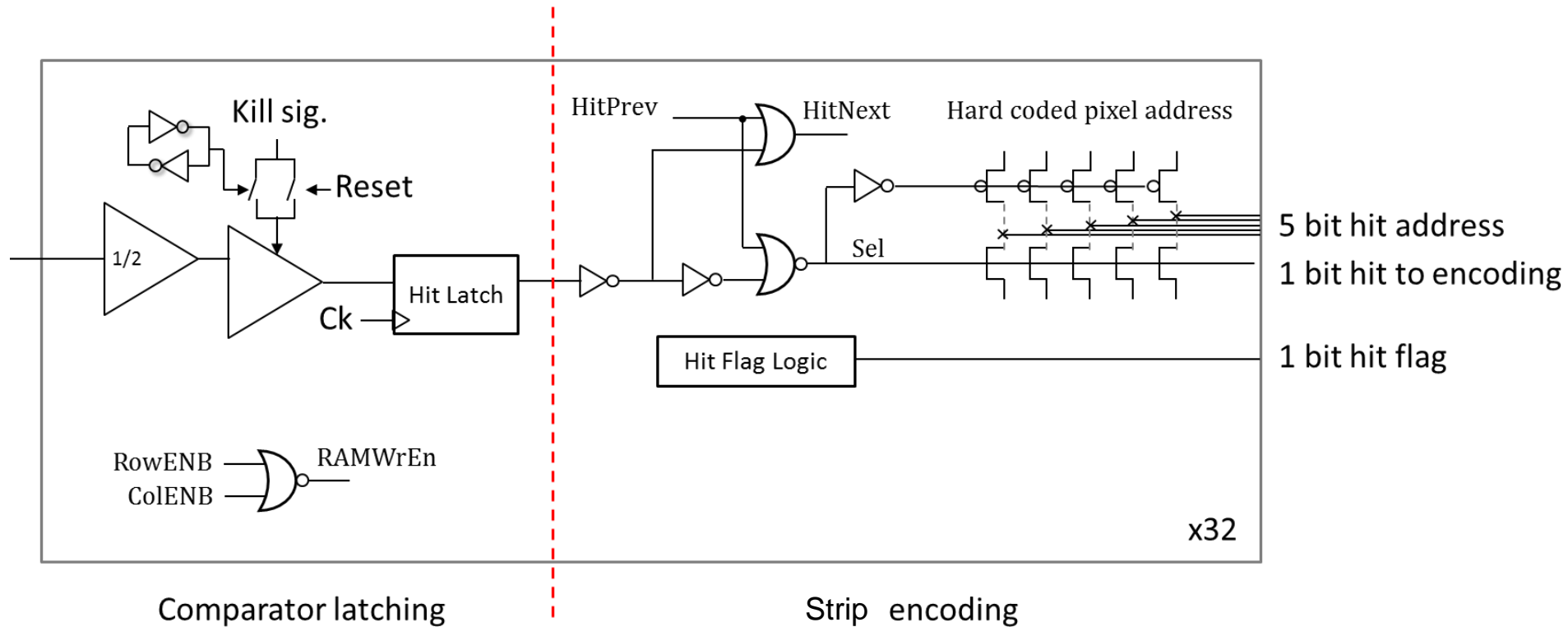


Serializer & LVDS TX/RX

CHESS2: Pixel



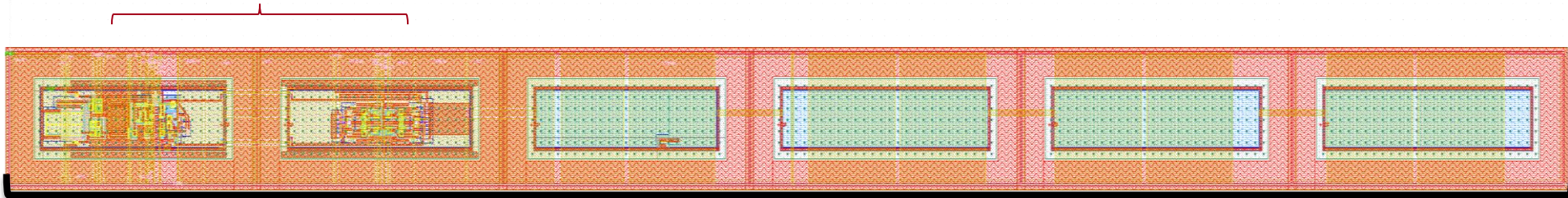
CHESS2: Pixel periphery schematic



- Encode the column address of the first hit and raise a flag if a double hit has occurred on the same strip

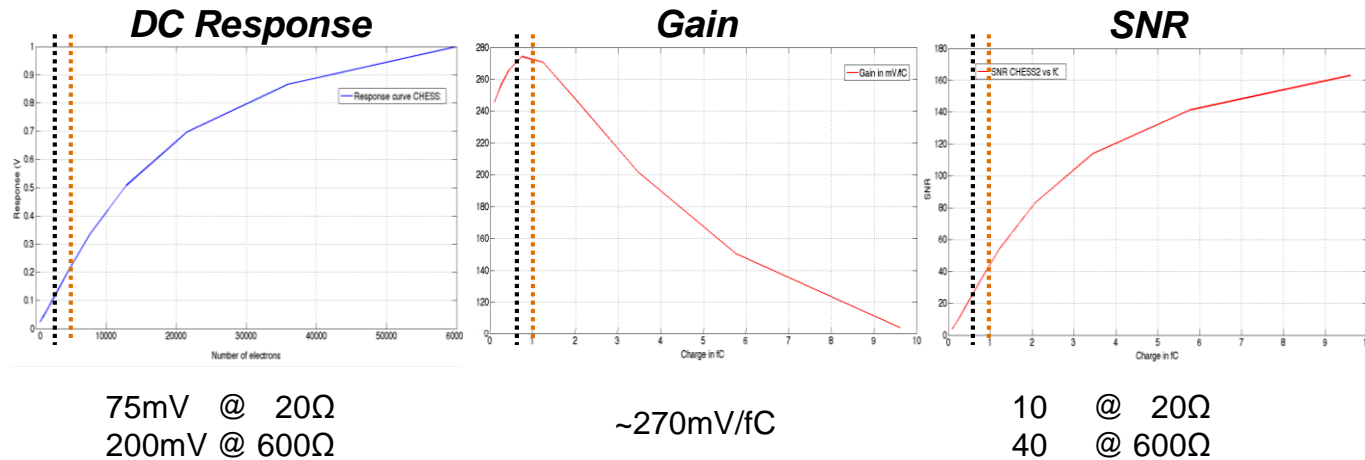
CHESS2: Pixel Layout – 630 μ m x 40 μ m

- Amplifier
- Half comparator
- Charge injection
- Pixel Selection
- Comparator Trimming Memory

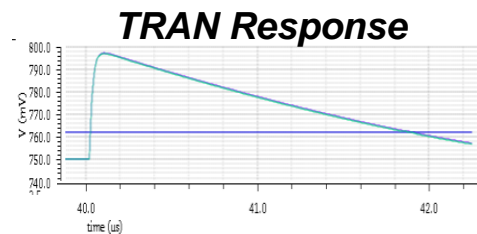


- 6 connected NWELLs
- 50% diode fraction
- P-contact around each NWELL
- 120V rules

CHESS2: Simulated Pixel Behavior

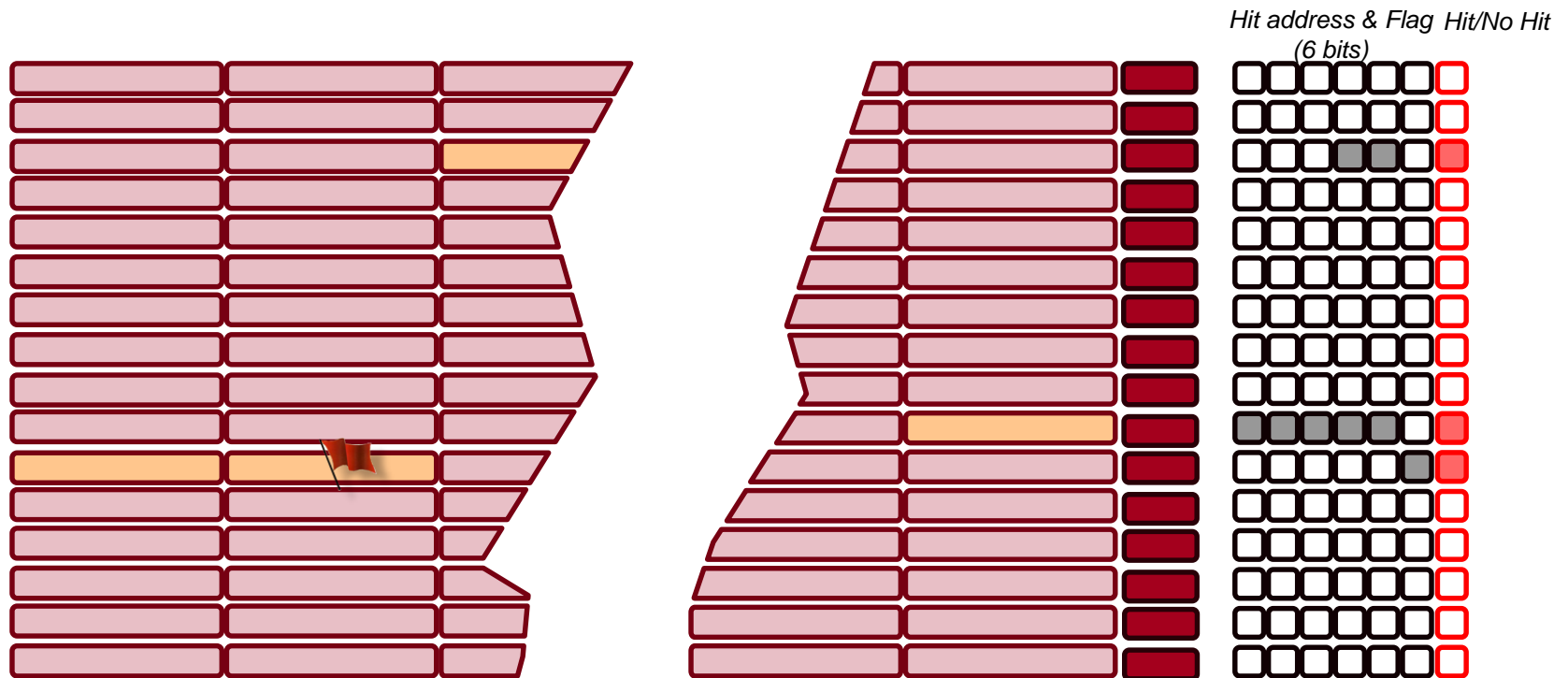


.....1MIP@ 20Ω
.....1MIP@ 600Ω
Equivalent charge at
different substrate
resistivity



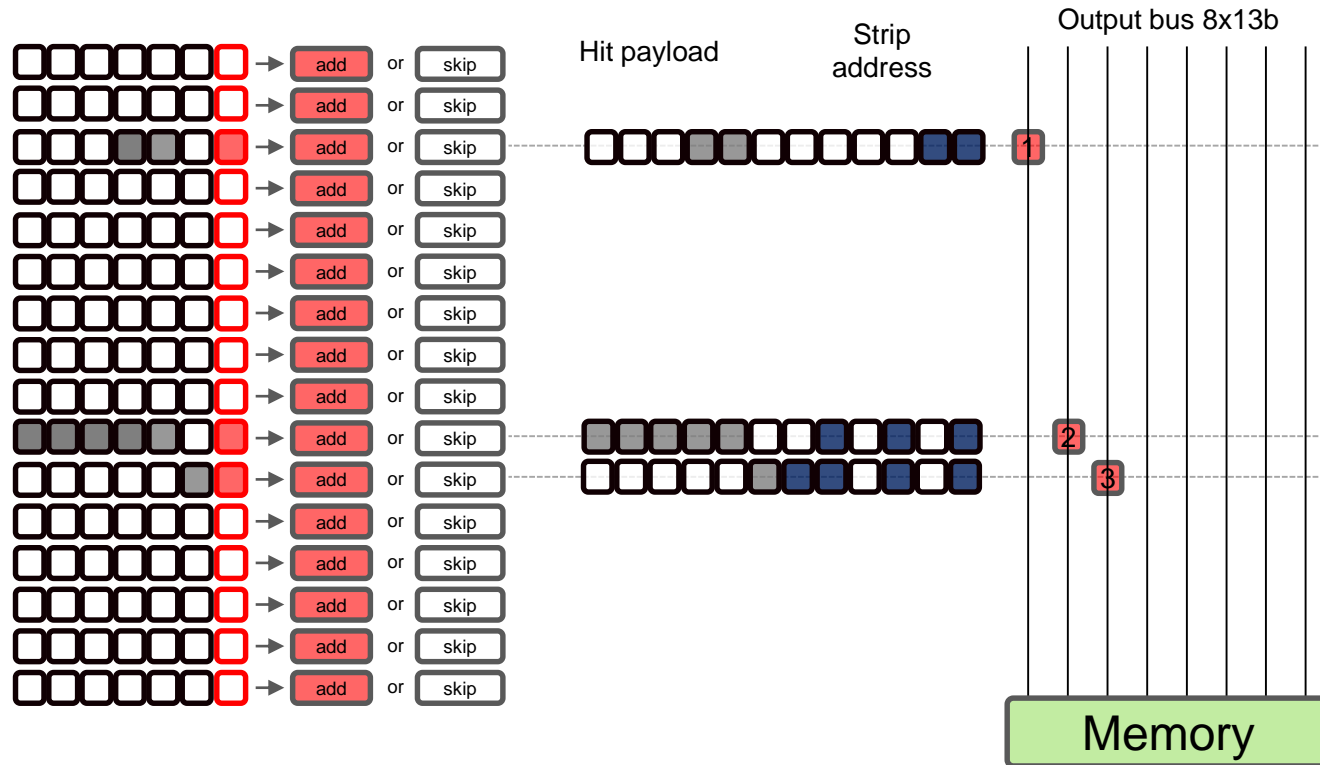
Less than 10ns walk time
~10ns peak time

CHESS2: Strip Encoding



1 hit per strip + flag in case of multiple hits. 5 + 1 bit
8 hits maximum per 128 strips. 7 bit

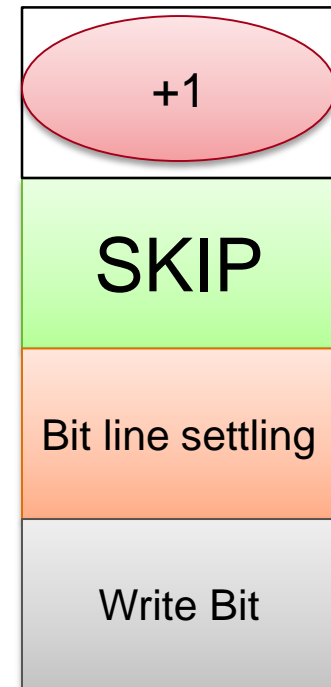
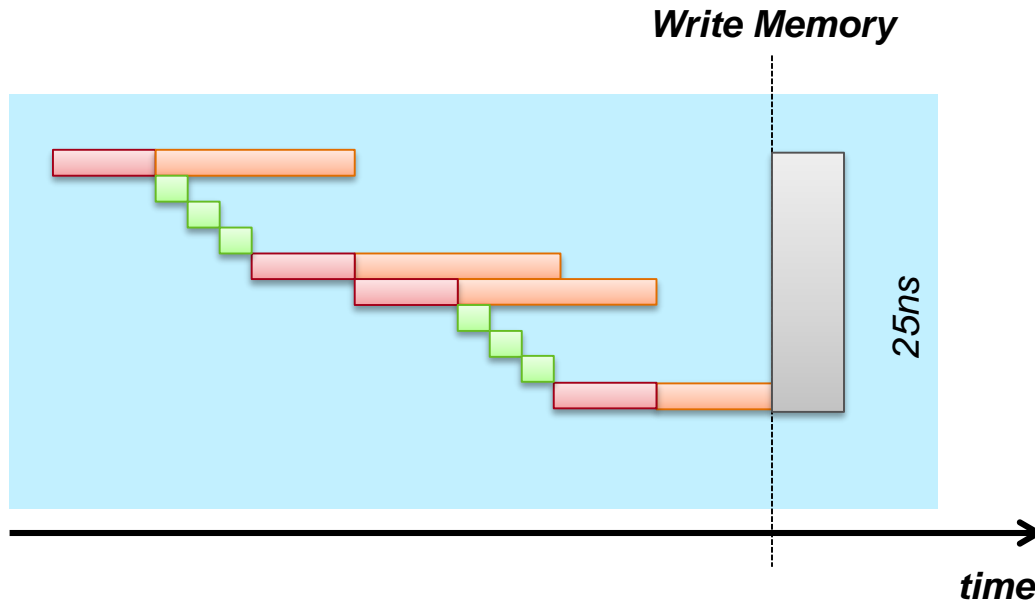
CHES2: Hit Encoding – Fast Skip Concepts



- Adder value used to multiplex data on 8 buses
- Overflow protection in 3b adder: 8 hits maximum
- Adder are slow (*up to 1ns in worst case speed*)
- *Huge load on the bit lines (127 switch off-capacitance + 5mm line capacitance)*

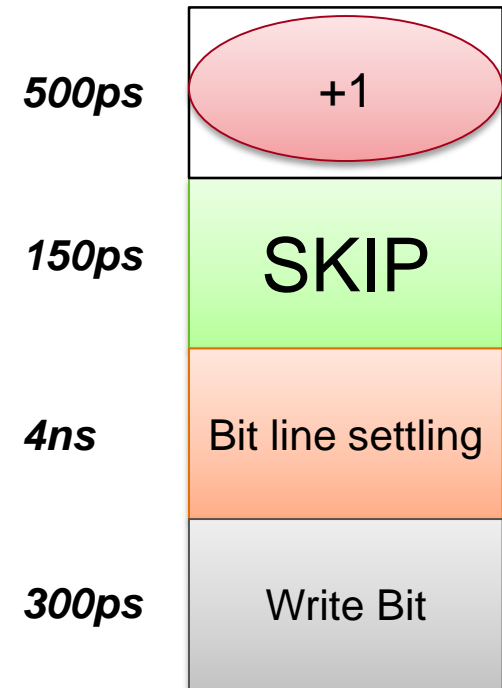
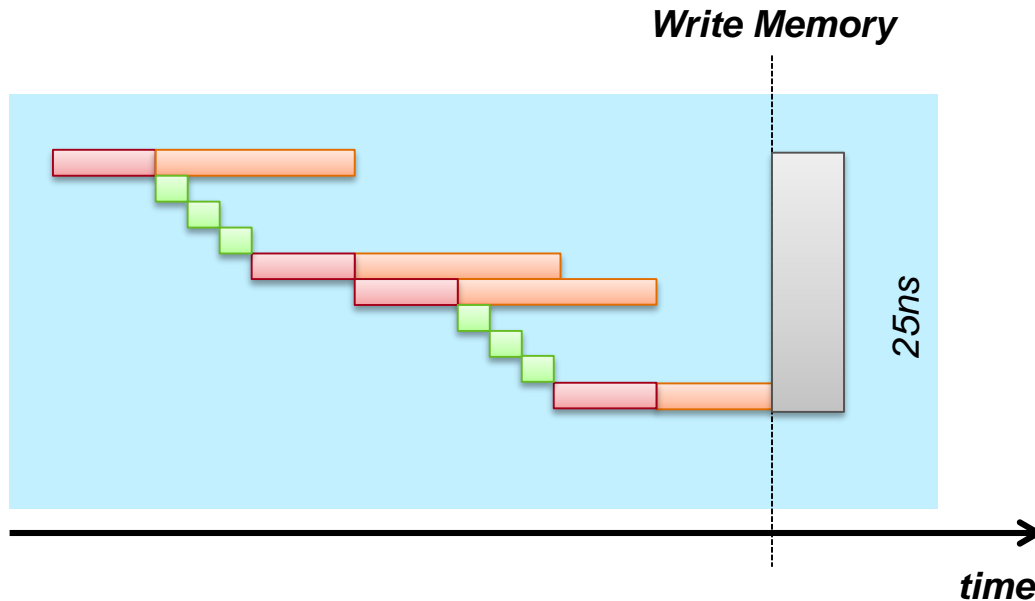
CHESS2: Hit Encoding – Fast Skip Concepts

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CHESS2: Hit Encoding – Fast Skip Concepts

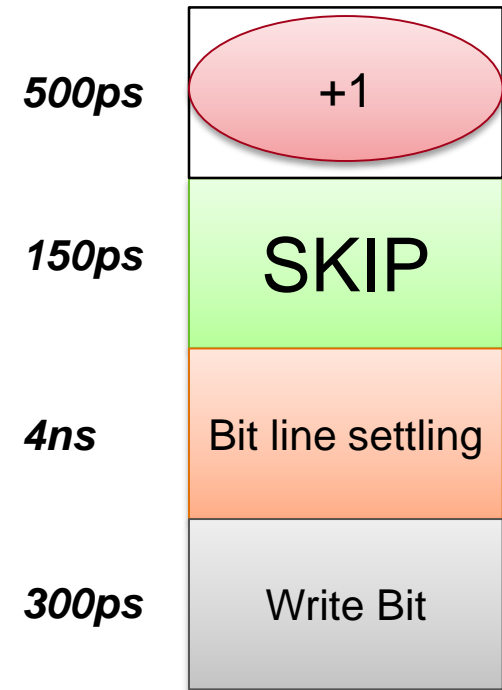
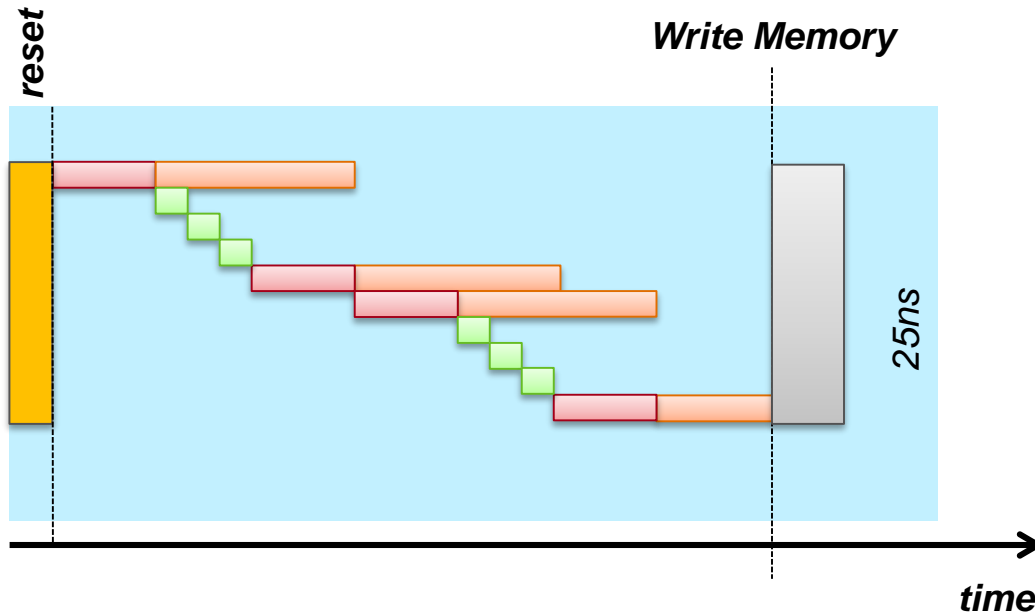


- Time to get the bit lines ready is based on number of hits
- Can be as high as 64ns if are all hits.



We are interested in the first 8 hits so the worst case using this architecture is when we have no hit on the first 120 rows and hit on the last 8 rows -> 22ns

CHESS2: Hit Encoding – Fast Skip Concepts



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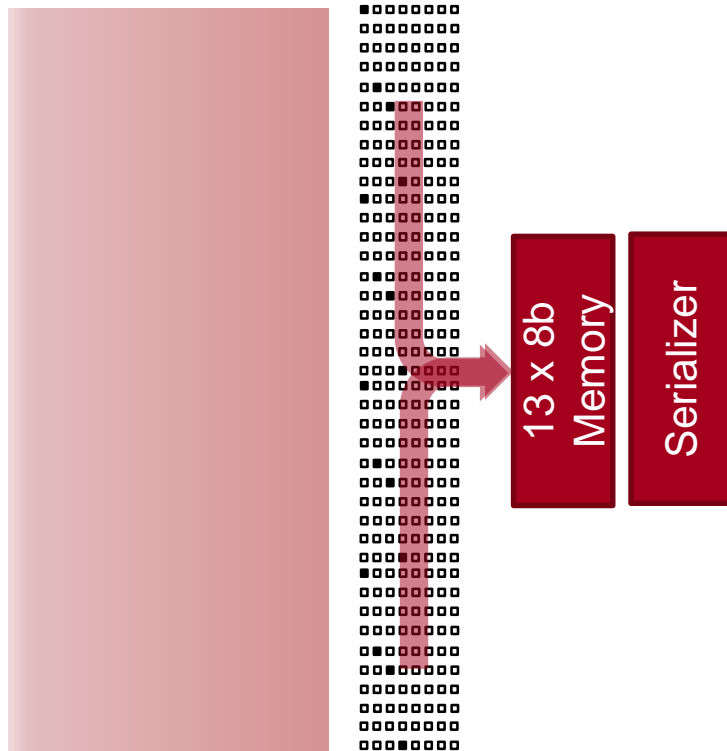
We are interested in the first 8 hits so the worst case using this architecture is when we have no hit on the first 120 rows and hit on the last 8 rows -> **22ns**



Avoid ghost from previous cycle introducing a **reset phase**

CHESS2: Hit Encoding – Fast Skip Concepts

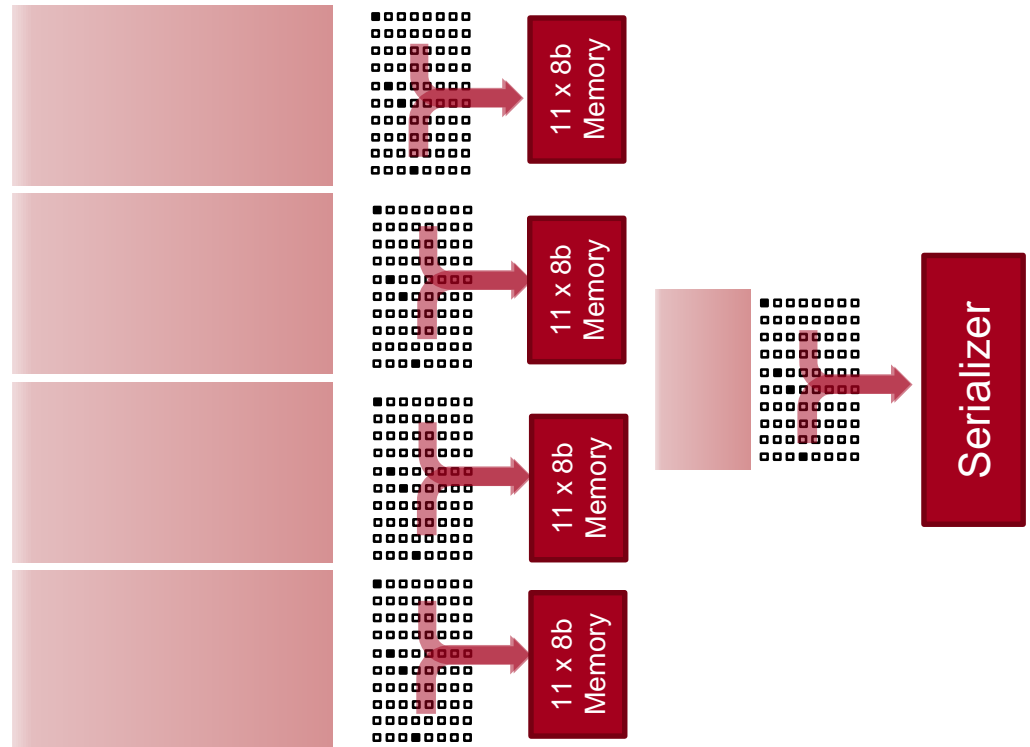
Find first 8 hits in 128 rows



Worst case scenario:

22ns

2x Find first 8 hits in 32 rows (2 stage in a pipeline-like behavior)

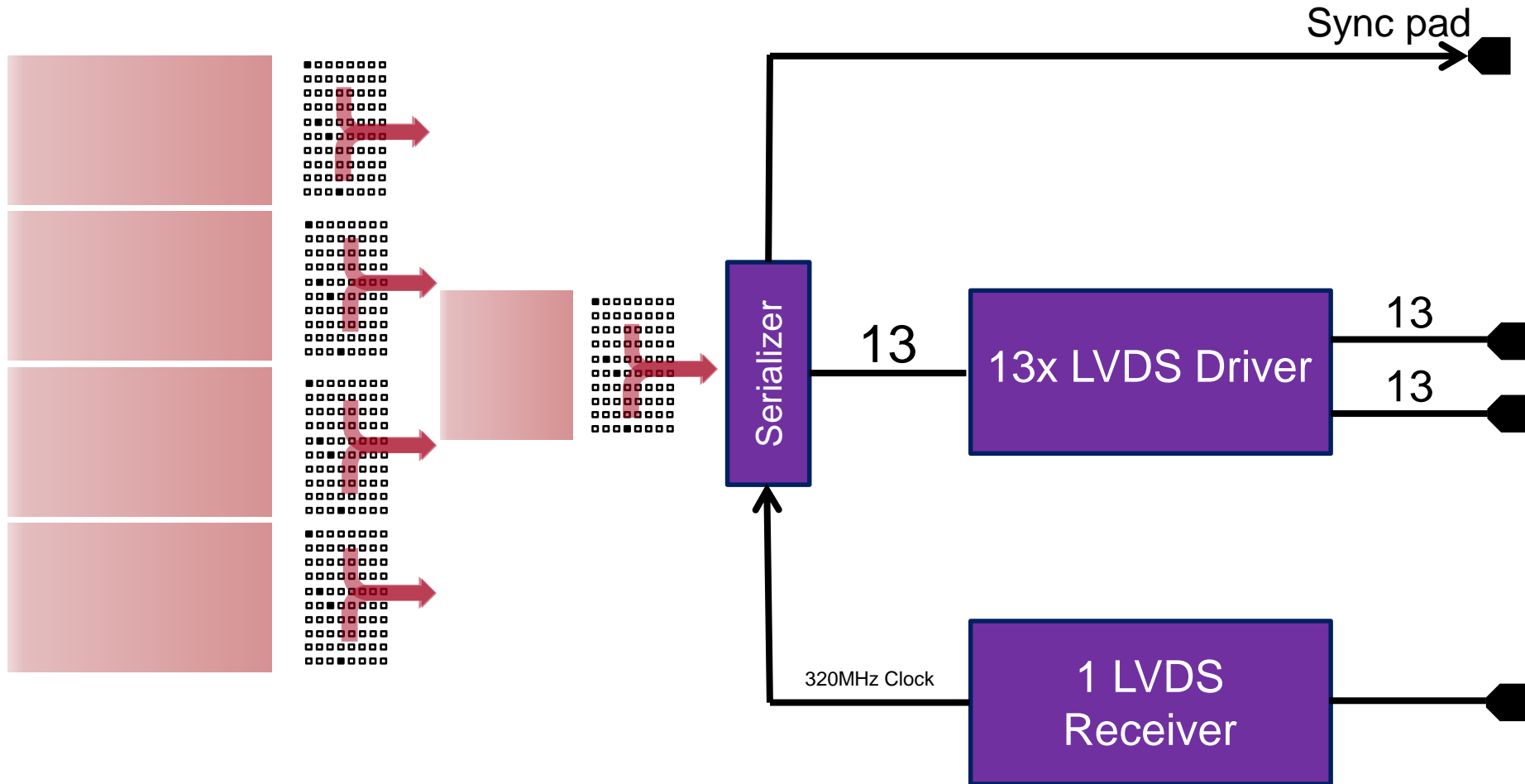


7.6ns

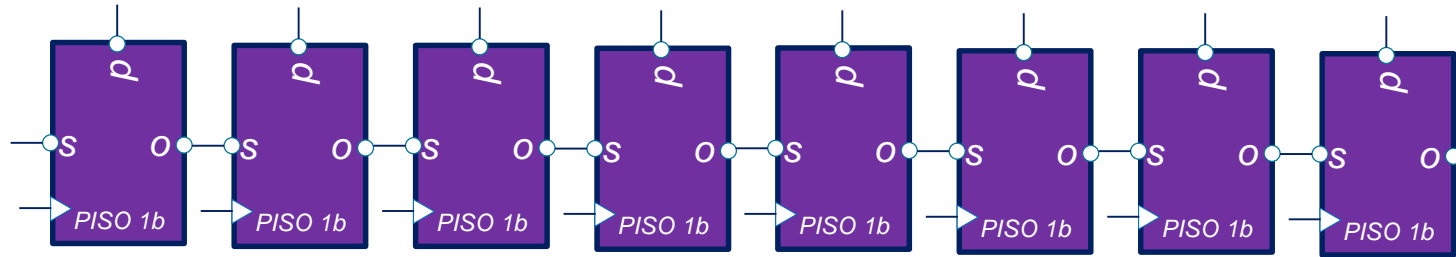
CHESS2: Fast Adder x32 (Layout)



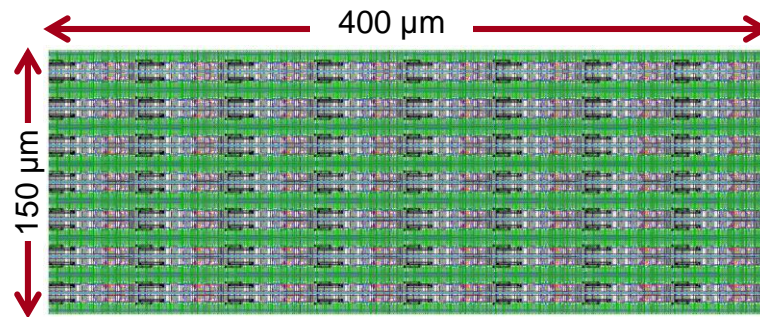
CHESS2: LVDS TX/RX and Sync



CHESS2: Serializer



- 8 x 13 1bit PISO Cell.
- Parallel input with 25ns period (synchronized to the 40MHz external clock).
- Serial Output has 3.125ns period (synchronized to the 320MHz external clock).



SLAC ASIC Control Interface (SACI)

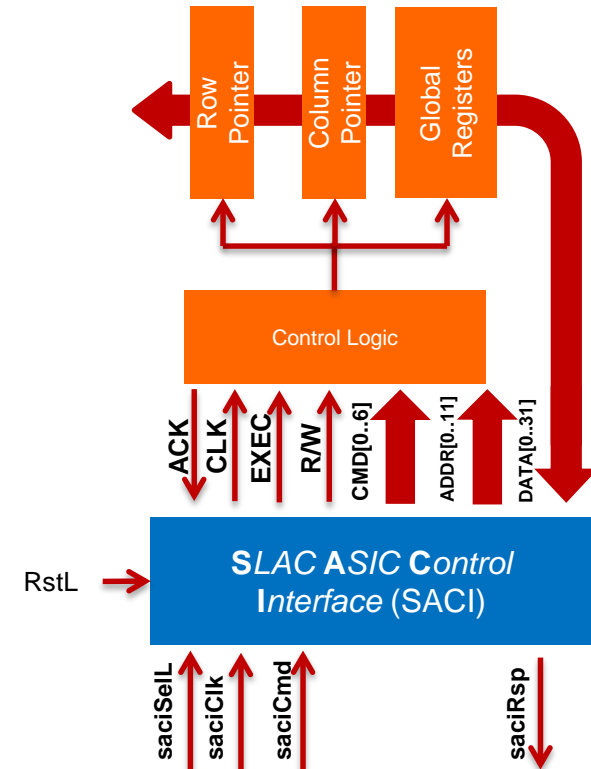
Serial Interface with handshake protocol

5 Signals

- 3 shared: *saciClk*, *saciCmd*, *saciRsp*.
 - 1 dedicated select line per slave: *saciSelL*.
 - 1 Reset Line (*RstL*) can be shared with the ASIC Global Reset.
-
- Operated between 0V and 3.3V
 - Allows multiple SACI on same bus (parallel mode).

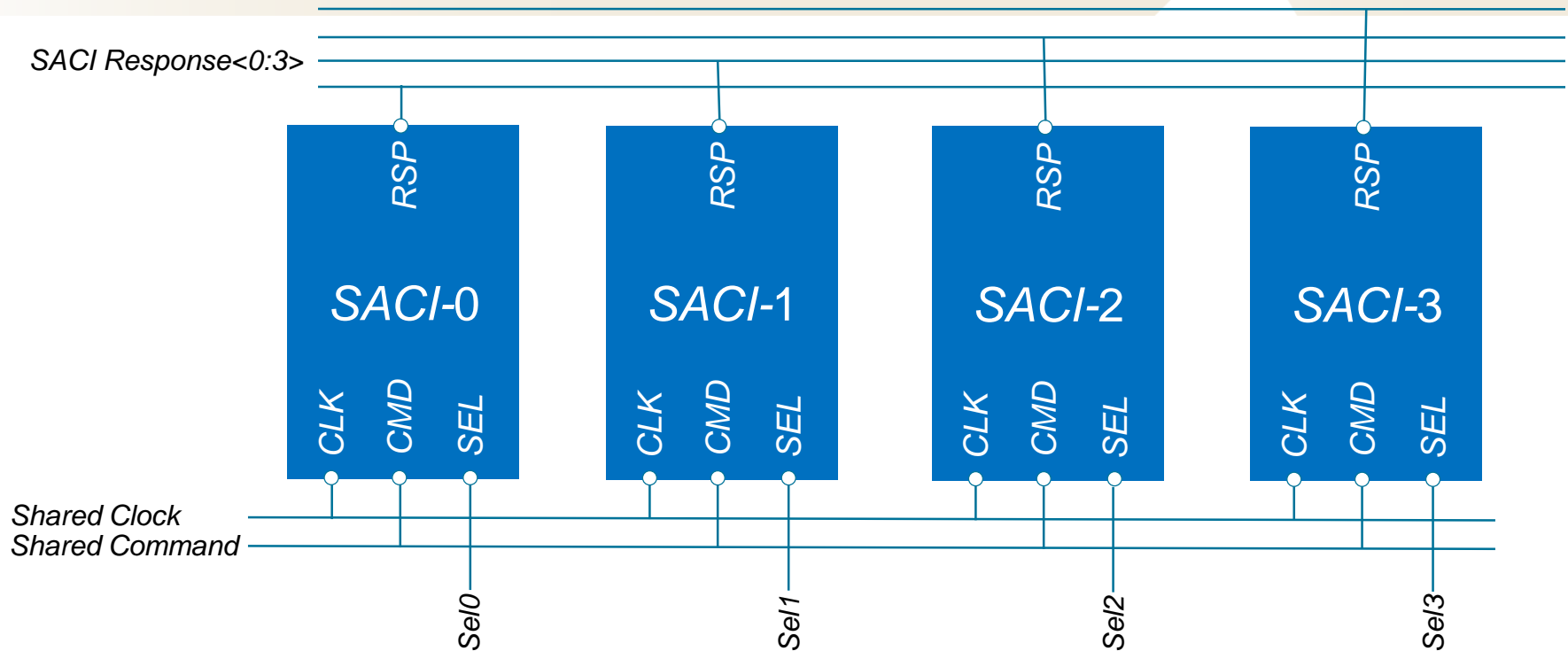
SACIcmd (serial signal):

—



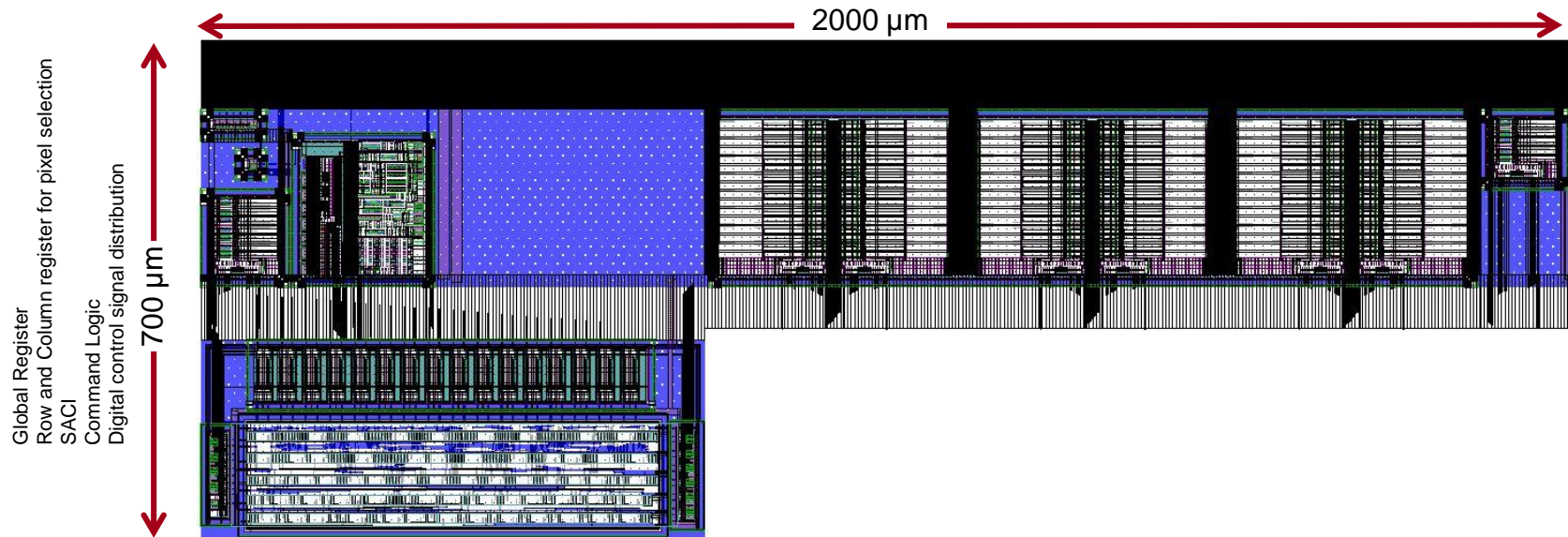
SACI – Multiple ASIC connection

SLAC

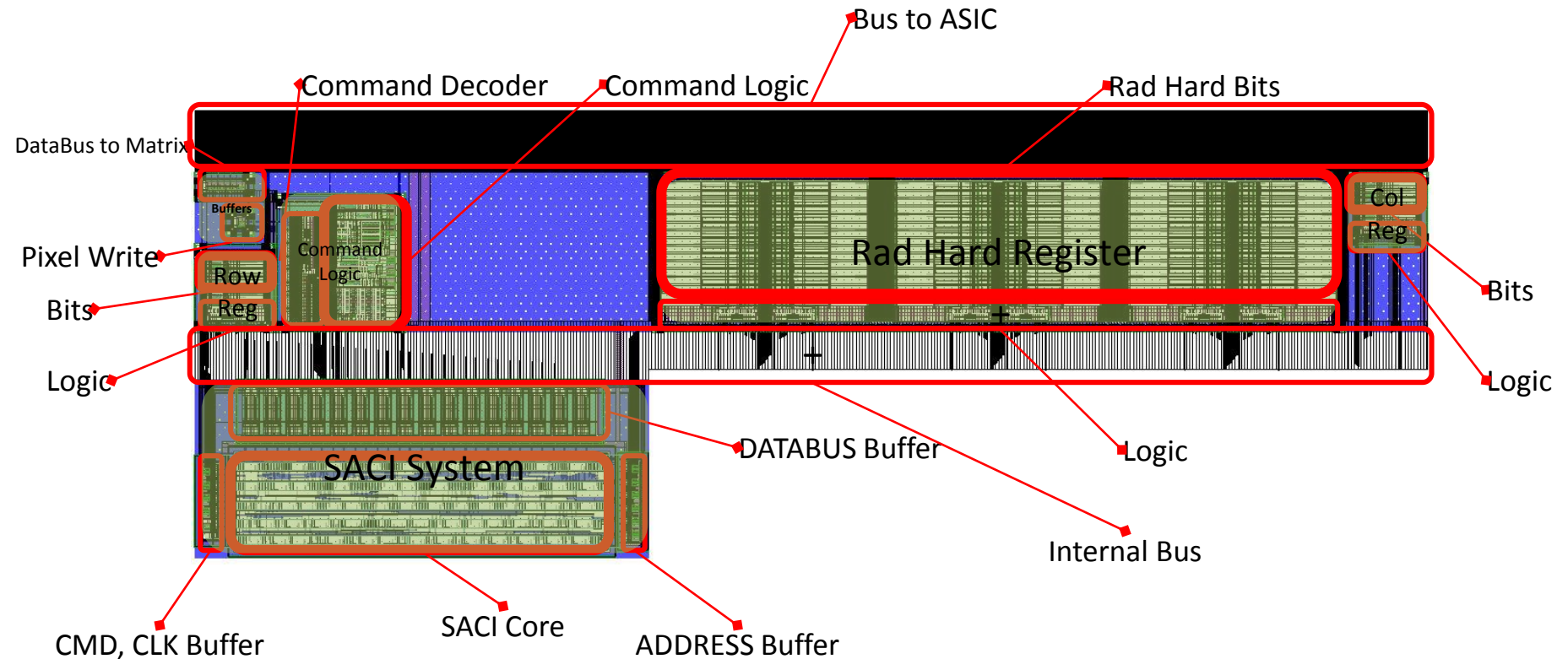


Response line can be shared if only 1 SACI is selected when the command arrives.

Control Unit



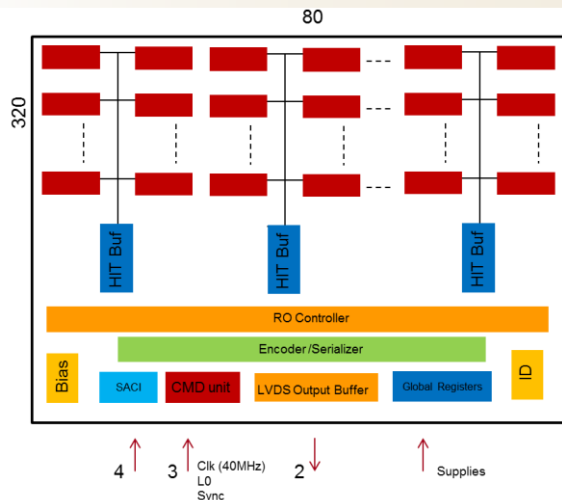
Control Unit



COOL-1: CMOS for Outer Layers ASIC

Can we build a full read-out system that meets the ATLAS pixels requirements (at least for the outer layers)?

SLAC



Tentative goals

Pixel size

Array

Full Size

Max. Signal

Effective ENC

DC Current cons.

COOL-1

250x50 μm^2

320x80

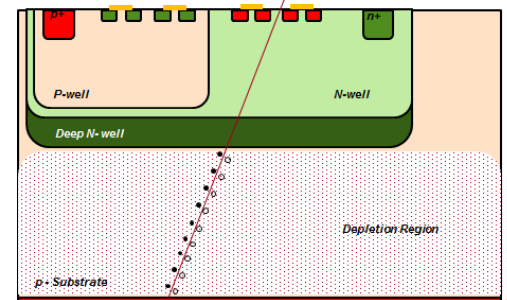
reticles

$\sim 10\text{ke}^-$

$< 120\text{e}^-$

$\sim 20\mu\text{A/pix}$

Large Potentials in ATLAS outer pixels 5th and 6th layers!



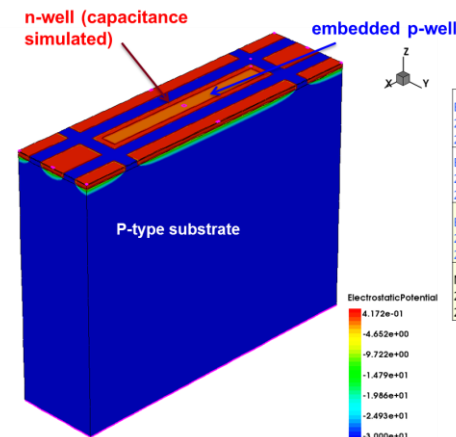
HR-fullCMOS structure

General characteristics

- Bunch timing and amplitude (ToT) extraction
- Column digital readout
- End-of Column hit buffers controlled by the L0 trigger (1MHz, 6 μm latency)
- System-on-chip approach (limited IO required)
- Serial LVDS readout
- SACI configuration protocol
- Calibration per pixel
- Auxiliary Monitoring

Objectives:

- Demonstrate HR-CMOS as a viable solution for complex circuit architectures (FEI3-like)
 - In-time efficient (95%) within 25ns
 - has a sufficient S/N ratio
 - has 50x250 μm^2 pixel
 - can cope with the expected hit rate
 - is low power $\sim 20\mu\text{A/pixel}$
 - can sustain 50 Mrads TID and 10^{15} neq/cm² NIEL



Baseline Pixel 250x50, nwell 230x30	n-well to internal p-well capacitance	330fF
Baseline Pixel 250x50, nwell 230x30	total n-well capacitance with internal p-well	400fF
Baseline Pixel 250x50, nwell 230x30	total n-well capacitance without internal p-well	70fF
Narrow diffusion: 250x50, nwell 220x20	total n-well capacitance without internal p-well	51fF

HR CMOS in LFoundry 0.15 μ m technology

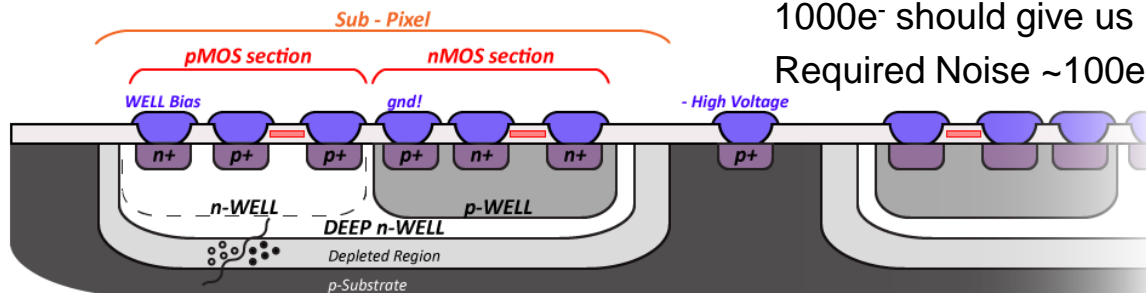
LF15A is a modular 0.15 μ m RF CMOS process, offering up to 6 levels of Al plus thick metal (2 - 6 μ m), optionally a MIM capacitor, a polyimide passivation and I/O voltages of 1.8 V, 3.3V and 5.0 V.

- Substrate resistivity 1-2k Ω cm
- Allow isolated NWELL within a DNWELL (Full CMOS)
- Large fill factor $\sim 85\%$ for 50x250 μm^2 pixel
- Break down voltage $\sim 120\text{V}$

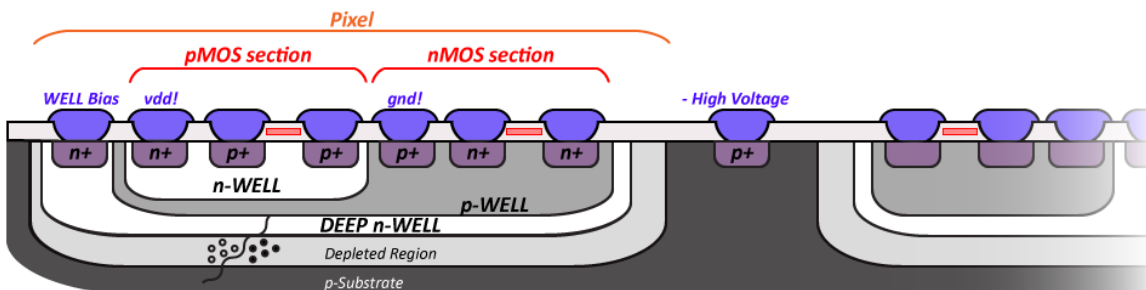
Thinned to 125 μ m:

- full depletion from the back side should be feasible (80V at 2k Ω cm)
- $Q_{\text{MIP}} \sim 10000e^-$
- $C_{\text{in}} \sim 400\text{fF}$ (70fF DNW to SUB, 330fF DNW to PW) for 50x250 μm^2 pixel (worst case)
- Considering sharing a threshold around $1000e^-$ should give us reasonable efficiency.

Required Noise $\sim 100e^-$



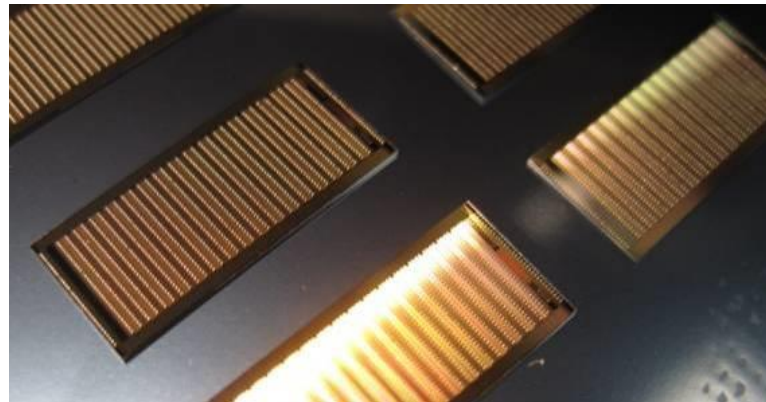
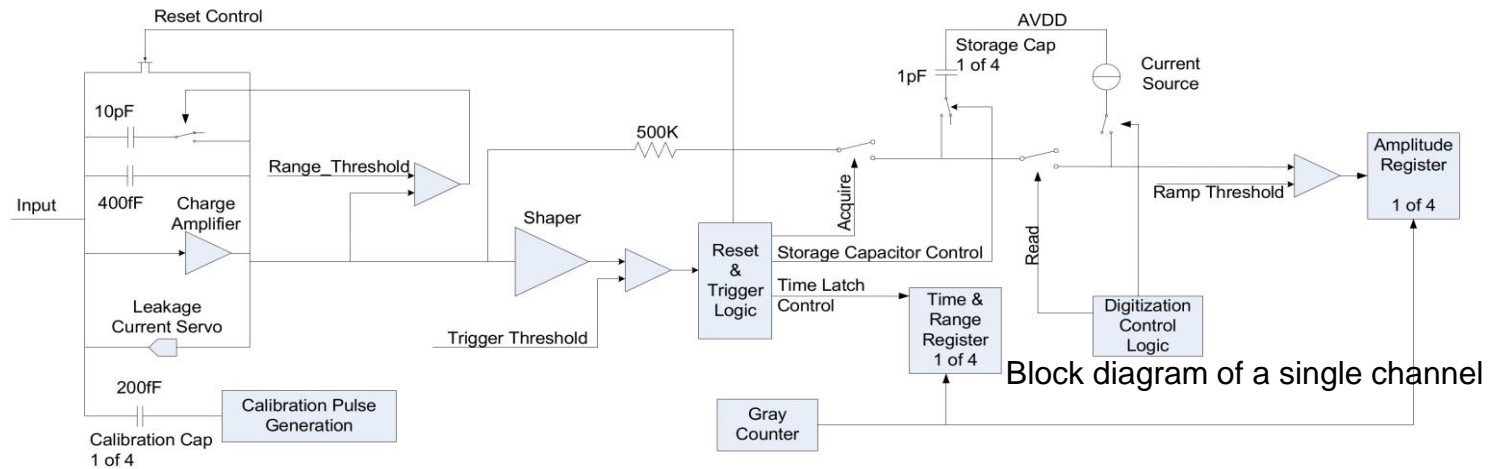
AMS 0.35 μ m HV



LF 0.15 μ m HR

KPiX ASIC: ECal read-out of Silicon Detector (SiD) for ILC

SLAC

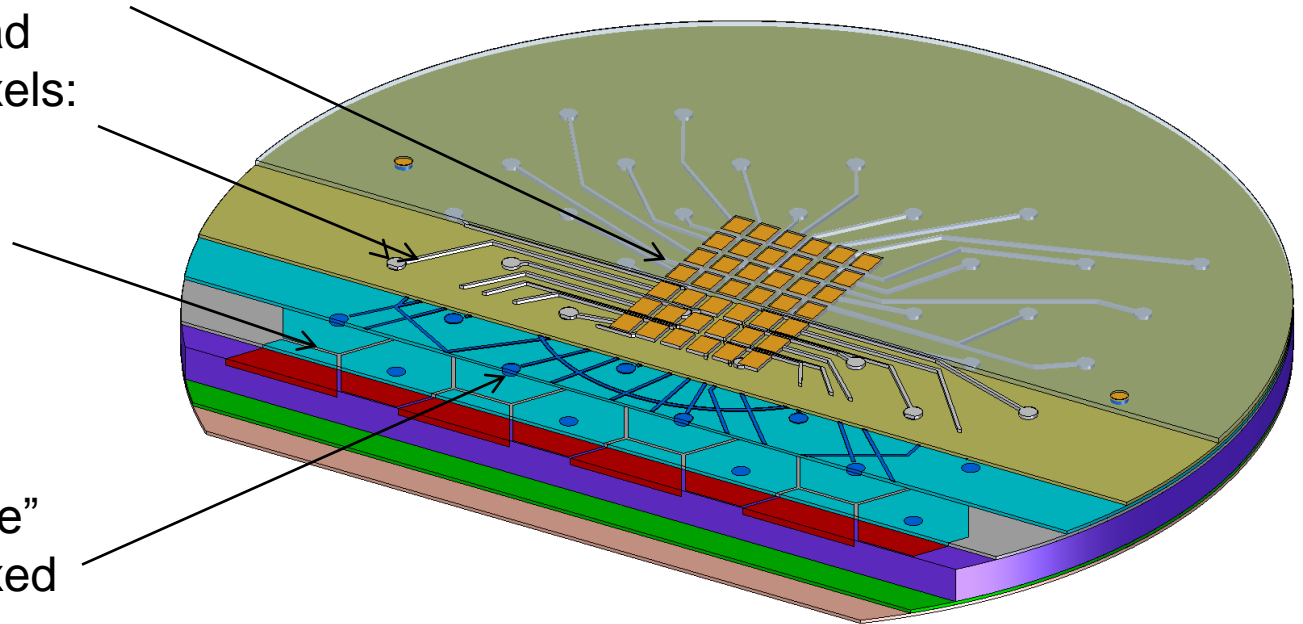


1024-channel KPiX

Sensor Traces

In present design, metal 2 traces from pixels to pad array run over other pixels: parasitic capacitances cause crosstalk.

New scheme has “same” metal 2 traces, but a fixed potential metal 1 trace shields the signal traces from the pixels.



The Ecal sensors are large hexagonal silicon sensors with a diameter of about 10cm segmented in little hexagons of ~5mm. KPix is bump bonded in the center and traces running on top of pixels fan out across the entire sensor

- Bump bonding to sensors with Al pads can be very difficult...
 - Consider sensor foundry build final pad stack.
 - Don't dice the sensors until bonding issues are fully controlled.
- EMCal can have huge number of pixels hit simultaneously, causing synchronous disturbances as pixels reset...Problem understood, small changes in KPiX design.
- Sensors plus ROC's can have issues with parasitic couplings...

Pixel size	KPiXM-Trk	KPiXM-Cal
Array	50x500 μm^2	1000x1000 μm^2
Full Size	200x2400	100x94
Max. Signal	Stitched 5x5 reticles	Stitched 5x5 reticles
Effective ENC	1fC	1pC
Filtering	<200e ⁻	<1000e ⁻
S/N	LP + CDS	LP + CDS
In pix mem. depth	>20	>4
ADC resolution	1 bucket	16 buckets
DC Power cons.	12 bits	12 bits
Power pulsing	~ 20 $\mu\text{W}/\text{pix}$	~ 20 $\mu\text{W}/\text{pix}$
	Yes	Yes

General characteristics

- Amplitude and Timing extraction on N bunches per train in each pixel (N=1 for the tracker, N=16 for the calorimeter)
- Synchronous (time-variant operation)
- Ultra-large Area beyond reticle size (stitching)
- System-on-chip approach (limited IO required)
- Platform based design
- Sparse readout
- Power Pulsing
- Calibration per pixel
- Temperature monitoring and tracking
- Auxiliary Monitoring

Pixel Matrix: fully analog.
Different designs for each detector variants

Balcony (kPiXM platform):

Analog BE:

- Bias
- Provides Calibration and Monitoring support

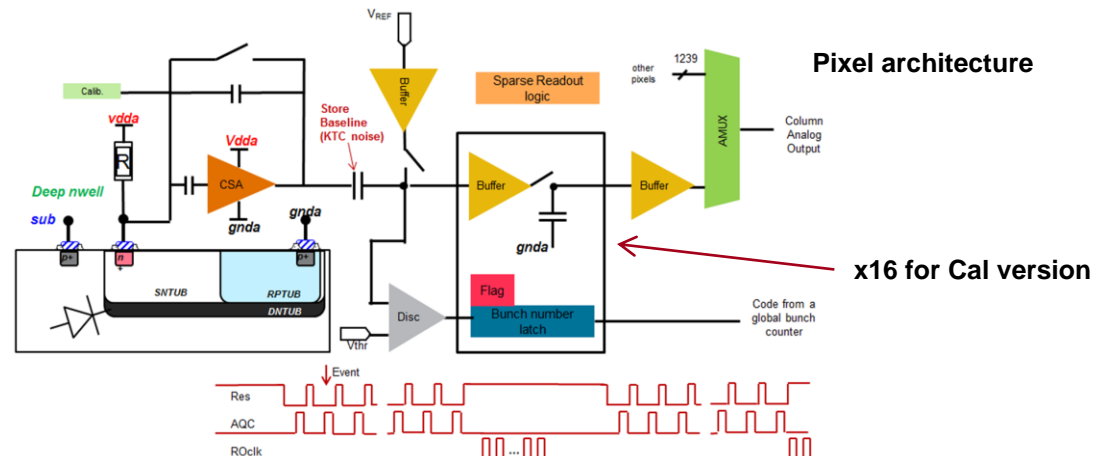
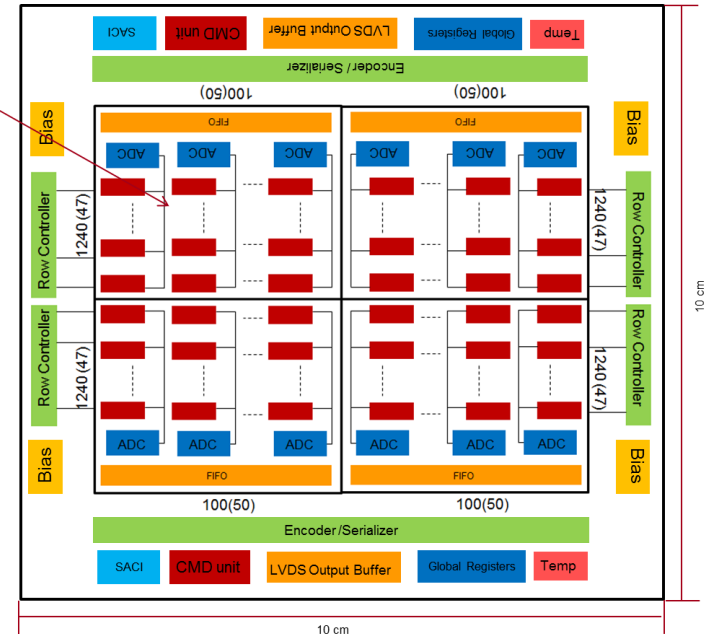
Mixed Signal BE:

- Performs Analog to Digital Conversion

Digital BE:

- Controls Configuration
- Controls Acquisition and Readout
- Serialize digital data

Large Potentials in SiD Trk and Ecal



- CHES2 is a full size demonstrator for the strip sensor in HVCMOS technology. In case of success it would significantly reduce strip sensor manufacturing cost, material budget, improve resolution, simplified readout chip.
- Fairly complicated chip with difficult layout and new process, design time took much longer than expected. In the top level layout stage and full chip simulations.
- Passive and Active pixel variants for COOL and KPiXM are under design.

Acknowledgements

We want to acknowledge for the work on CHESS the contribute of all the people involved in design, test and characterization of the devices.

Strip CMOS Author list

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And our sponsors:

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Backup Slides

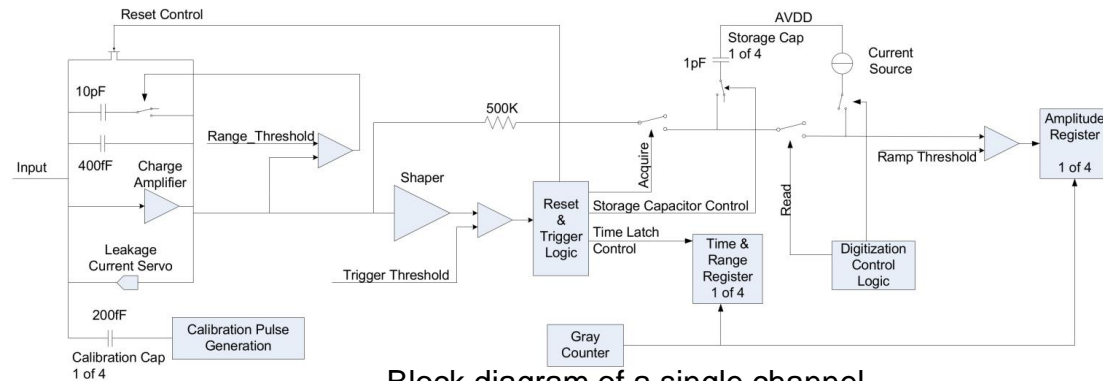
KPiX ASIC: ECal read-out of Silicon Detector (SiD) for ILC

SLAC

32×32 array = 1024 channels

Designed to be

- bump-bonded to a Si sensor, or
- bumped to a hybrid for large area detectors (RPC's, GEM's, etc)

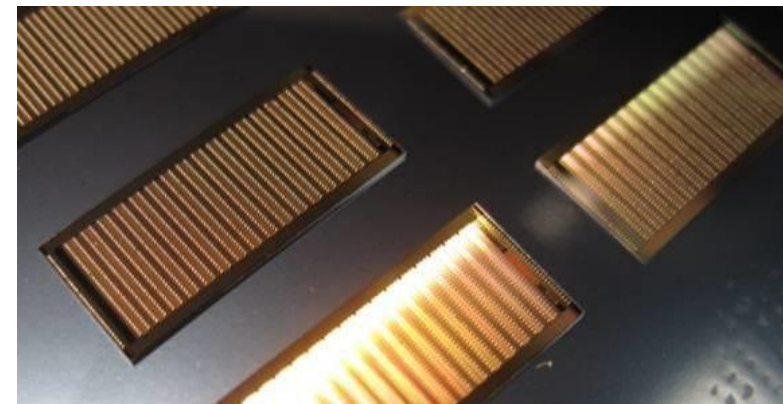


For each channel of the system-on-chip

- » 4 samples per train with individual timestamps
- » auto-triggering
- » internal per-channel 13-bit ADC
- » automatic range switching for large charge depositions (10pC)
- » bias current servo for DC coupled sensors
- » power cycling: power down during inter-train gaps (20 uW avg for ILC time structure)
- » built-in calibration
- » nearest neighbor trigger ability
- » high-gain feedback capacitor for tracker application
- » dual polarity for GEM and RPC applications
- » external trigger for test beam

Digital IP core with serial data IO (only 4 signals)

0.25μm TSMC



1024-channel KPiX